

AOL1418
N-Channel Enhancement Mode Field Effect Transistor
General Description

The AOL1418 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance. This device is ideally suited for use as a high side switch in CPU core power conversion.

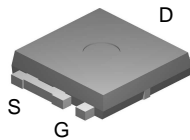
- RoHS Compliant
- Halogen and Antimony Free Green Device*

Features

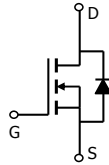
V_{DS} (V) = 30V
 I_D = 85A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 6 m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 10.5m Ω (V_{GS} = 4.5V)

UIS Tested
 Rg,Ciss,Coss,Crss Tested

UltraSO-8™ Top View



Bottom tab
 connected to
 drain


Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^B	I_D	$T_C=25^\circ\text{C}$ ^G	A
		$T_C=100^\circ\text{C}$	
Pulsed Drain Current ^I	I_{DM}	200	
Continuous Drain Current ^G	I_{DSM}	$T_A=25^\circ\text{C}$	W
Current ^G		$T_A=70^\circ\text{C}$	
Avalanche Current ^C	I_{AR}	30	A
Repetitive avalanche energy $L=0.3\text{mH}$ ^C	E_{AR}	135	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	W
		$T_C=100^\circ\text{C}$	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10\text{s}$	14.4	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	37	$^\circ\text{C/W}$
Maximum Junction-to-Case ^C	$R_{\theta JC}$	1	1.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.4	2.2	2.6	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	200			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		5 6.7	6 8.1	mΩ
		V _{GS} =4.5V, I _D =20A		8.3	10.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		60		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.72	1	V
I _S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz	1050	1320	1600	pF
C _{oss}	Output Capacitance		533			pF
C _{rss}	Reverse Transfer Capacitance		154			pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.95	1.5	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =20A		26	32	nC
Q _g (4.5V)	Total Gate Charge		13.3	16.2	nC	
Q _{gs}	Gate Source Charge		3.2		nC	
Q _{gd}	Gate Drain Charge		6.6		nC	
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		7.2	10	ns
t _r	Turn-On Rise Time		12.5	18	ns	
t _{D(off)}	Turn-Off Delay Time		22	33	ns	
t _f	Turn-Off Fall Time		6	9	ns	
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		29.7	36	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		29	36	nC

A: The value of R_{θJA} is measured with the device in a still air environment with T_A =25°C.

B: The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.

G: The maximum current rating is limited by bond-wires.

H: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

I: Pulse test; pulse width<=300us, duty cycle<=0.5%

* This device is guaranteed green after date code 8P11 (June 1ST 2008)

Rev6:May 2010

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

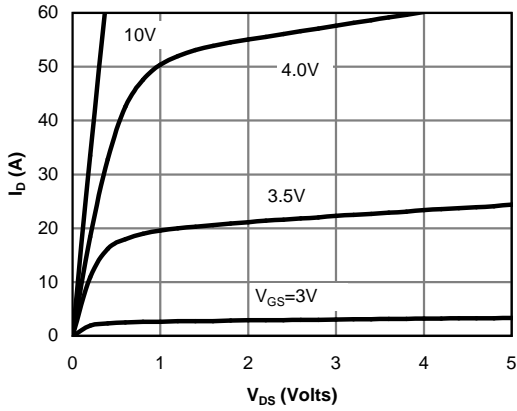


Fig 1: On-Region Characteristics

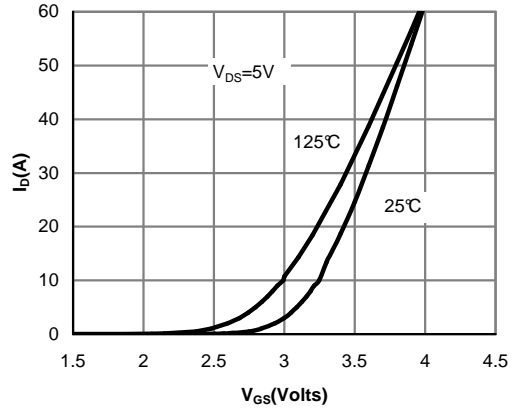


Figure 2: Transfer Characteristics

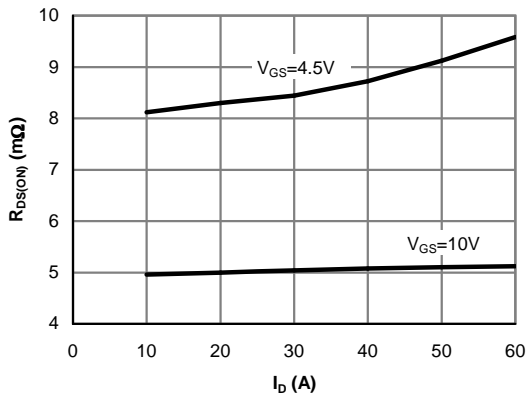


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

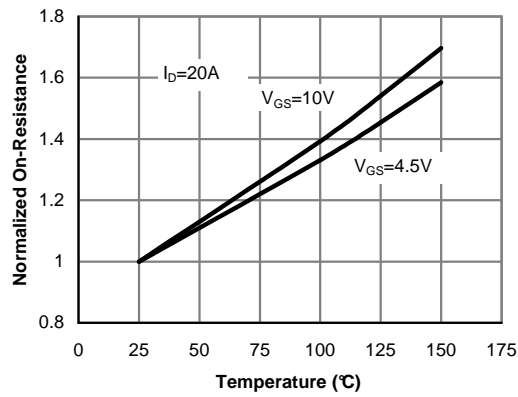


Figure 4: On-Resistance vs. Junction Temperature

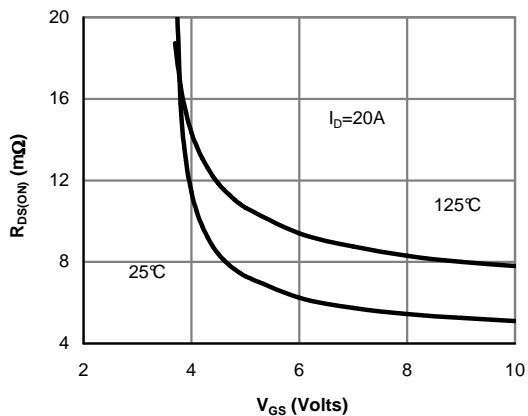


Figure 5: On-Resistance vs. Gate-Source Voltage

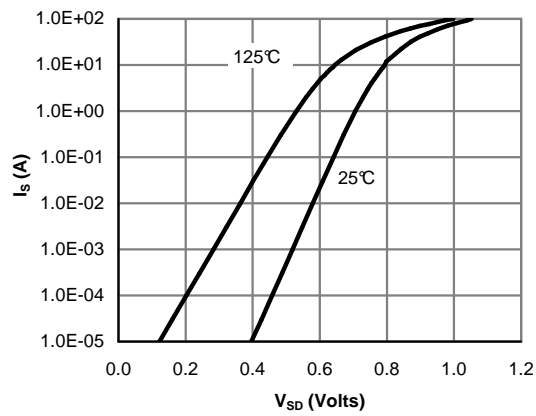


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

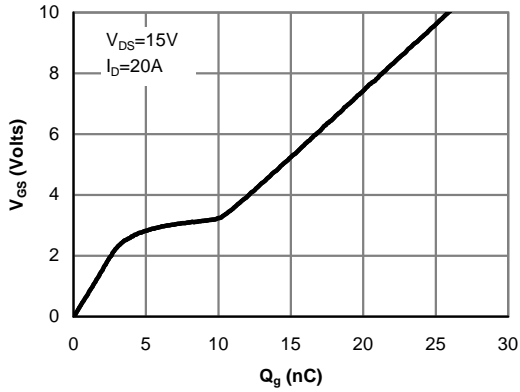


Figure 7: Gate-Charge Characteristics

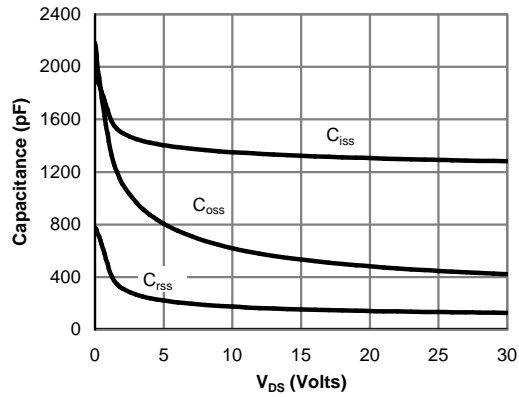


Figure 8: Capacitance Characteristics

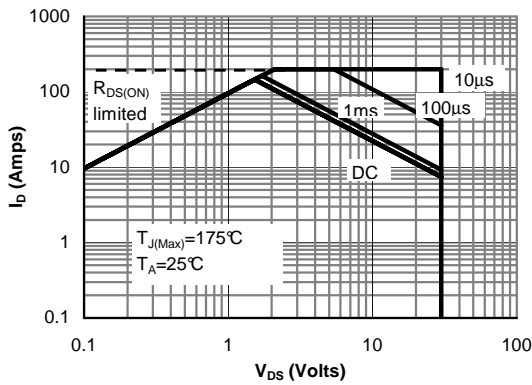


Figure 9: Maximum Forward Biased Safe Operating Area (Note H)

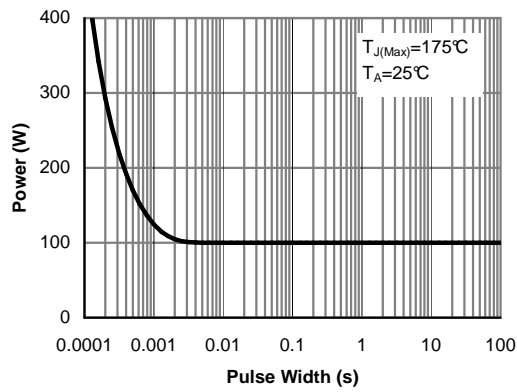


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

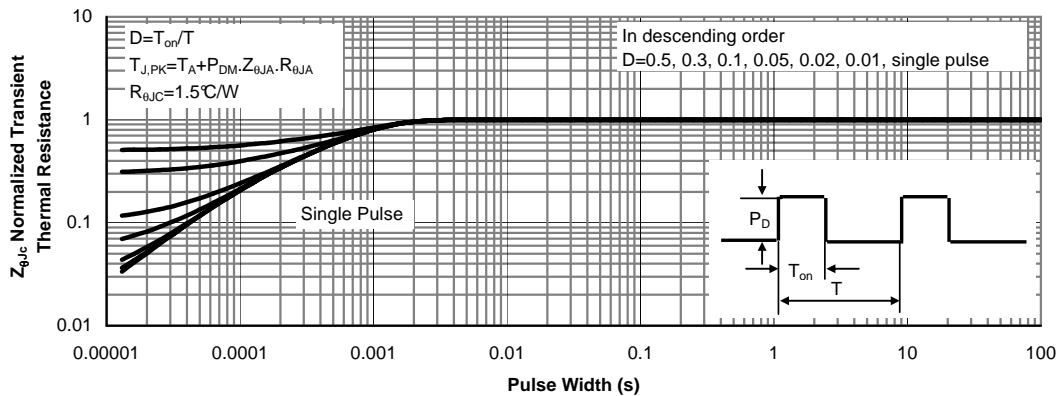


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

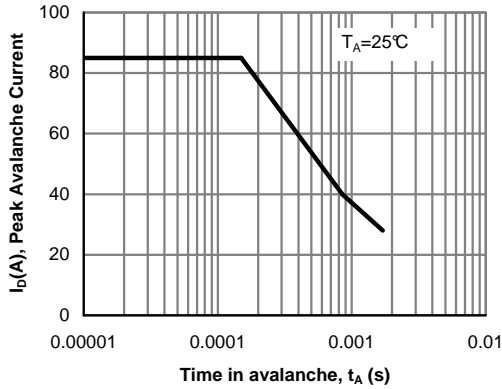


Figure 12: Single Pulse Avalanche capability

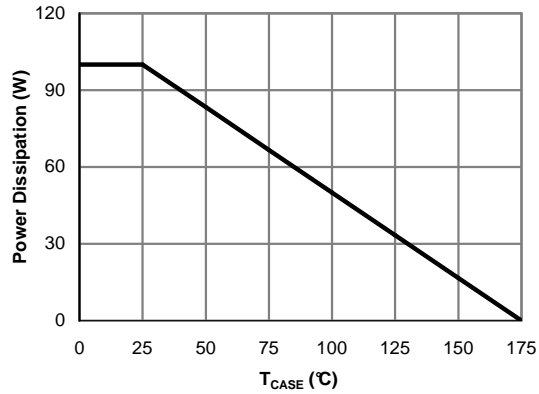


Figure 13: Power De-rating (Note B)

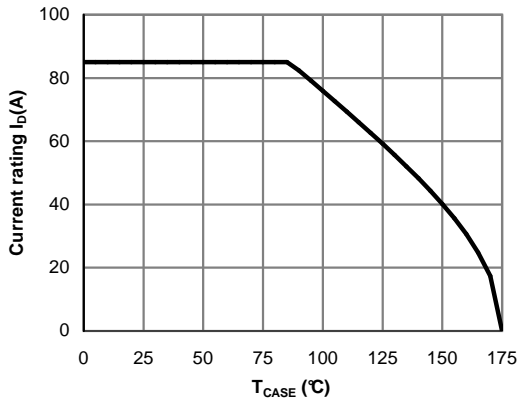


Figure 14: Current De-rating (Note B)

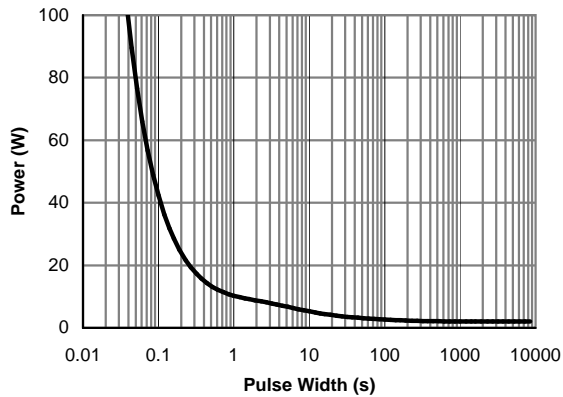


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

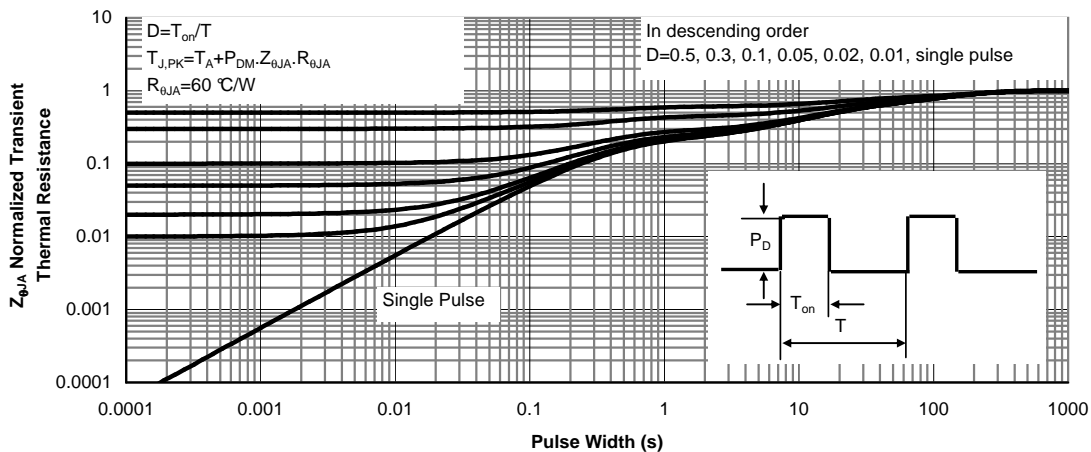
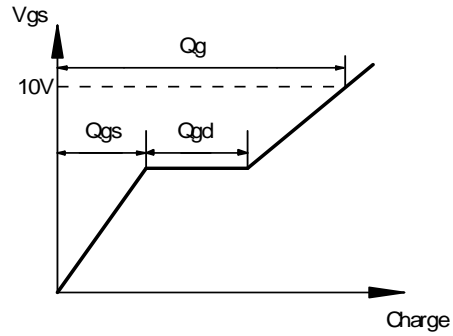
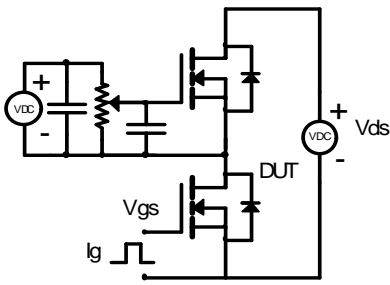
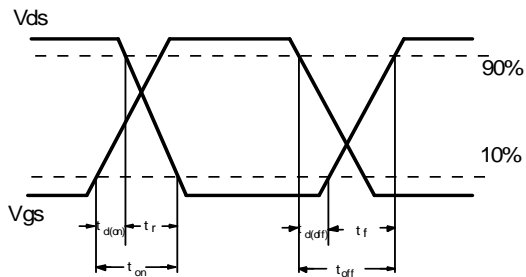
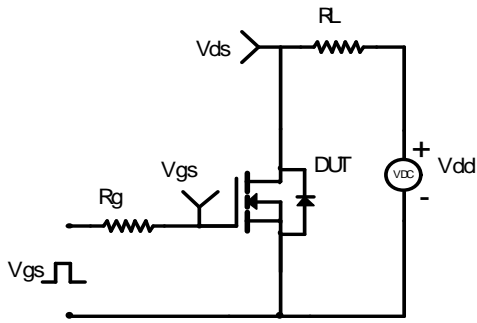


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

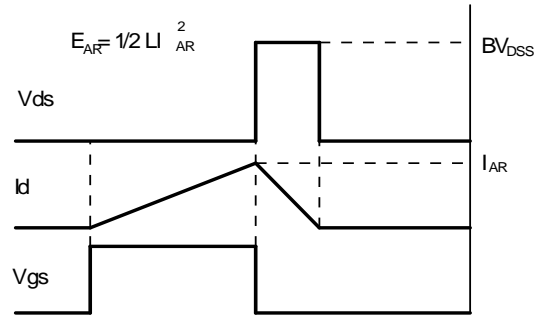
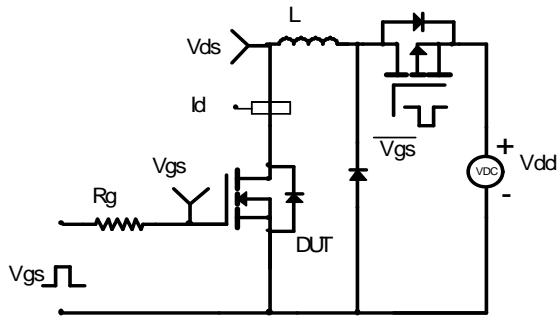
Gate Charge Test Circuit & Waveform



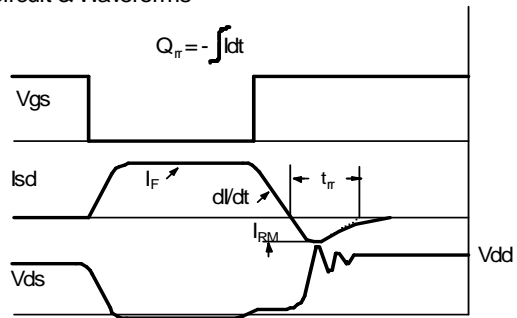
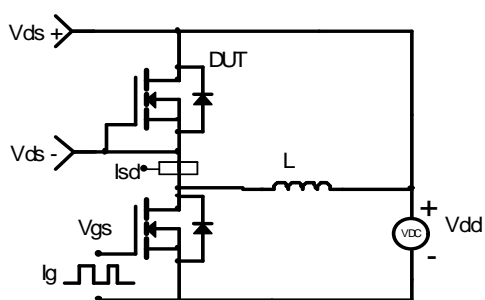
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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